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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/654,226	09/02/2003	Ammar Derraa	3882.8US (99-0017.08/US)	4741
24247	7590 06/15/2004		EXAM	INER
TRASK BRI	TT		SANTIAGO, MARICELI	
P.O. BOX 255	0			
SALT LAKE	CITY, UT 84110		ART UNIT	PAPER NUMBER
	•		2879	
			DATE MAILED: 06/15/2004	1

Please find below and/or attached an Office communication concerning this application or proceeding.

	<del></del>	Application No.	Applicant(s)		
		10/654,226	DERRAA, AMMAR		
	Office Action Summary	Examin r	Art Unit	)	
		Mariceli Santiago	2879	pw	
Period fo	The MAILING DATE of this communication or Reply	appears on the cover sheet wi	th the correspondence add	ress	
THE - External after - If the - If NC - Failu	ORTENED STATUTORY PERIOD FOR REMAILING DATE OF THIS COMMUNICATIOnsions of time may be available under the provisions of 37 CFI SIX (6) MONTHS from the mailing date of this communication a period for reply specified above is less than thirty (30) days, are period for reply is specified above, the maximum statutory period for reply within the set or extended period for reply will, by streply received by the Office later than three months after the med patent term adjustment. See 37 CFR 1.704(b).	N. R 1.136(a). In no event, however, may a r n. a reply within the statutory minimum of thirt eriod will apply and will expire SIX (6) MON tatute, cause the application to become AB	reply be timely filed by (30) days will be considered timely. THS from the mailing date of this combandoned (35 U.S.C. § 133).	nmunication.	
Status					
1)⊠	Responsive to communication(s) filed on 0	<u> 4 March 2004</u> .		_	
,	<i>,</i> —	This action is non-final.			
3)	3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.				
Dispositi	on of Claims				
5)□ 6)⊠ 7)□	Claim(s) 1-18 is/are pending in the applicated 4a) Of the above claim(s) is/are with Claim(s) is/are allowed.  Claim(s) 1-18 is/are rejected.  Claim(s) is/are objected to.  Claim(s) are subject to restriction are	drawn from consideration.			
Applicati	ion Papers				
10)⊠	The specification is objected to by the Example The drawing(s) filed on <u>02 September 2003</u> Applicant may not request that any objection to Replacement drawing sheet(s) including the control of the oath or declaration is objected to by the	is/are: a) accepted or b) the drawing(s) be held in abeyar rrection is required if the drawing	nce. See 37 CFR 1.85(a). (s) is objected to. See 37 CFF	R 1.121(d).	
Priority (	ınder 35 U.S.C. § 119				
<ul> <li>12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).</li> <li>a) All b) Some * c) None of:</li> <li>1. Certified copies of the priority documents have been received.</li> <li>2. Certified copies of the priority documents have been received in Application No</li> <li>3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> </ul>					
Attachmen					
· <del>==</del>	1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  4) Interview Summary (PTO-413)  Paper No(s)/Mail Date				
3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)  Paper No(s)/Mail Date  5) Notice of Informal Patent Application (PTO-152)  6) Other:					

Art Unit: 2879

#### **DETAILED ACTION**

## Response to Amendment

The Amendment, filed on March 4, 2004, has been entered and acknowledged by the Examiner.

Claims 1-18 are pending in the instant application.

## **Double Patenting**

The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970);and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

Claims 1-18 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 1, 10 and 14 of U.S. Patent No. 6,326,222. Although the conflicting claims are not identical, they are not patentably distinct from each other for the following reasons.

U.S. Application	U.S. Patent	Reasons for rejection under obviousness-type double patenting
SN 10/654,226	No. 6,326,222	
Claim 1	Claim 1	Patent '222 claims a method of fabricating at least one emission
		structure, comprising forming at least one conductive structure
		extending across at least a portion of a substrate, substantially
		removing a longitudinal portion of the at least one conductive
		structure (patterning) to define at least one conductive layer
		substantially perpendicular (parallel rows) to the substrate, the

Art Unit: 2879

<del></del>	<u> </u>	substrate being exposed along a length of the at least one
		conductive layer, and forming at least one emission structure
		adjacent the at lest one conducive layer.
Claim 2	Claim 1	Patent '222 claims a method wherein the at least one emission
		structure includes an emitter tip.
Claim 3	Claim 1	Patent '222 claims a method wherein the at least one emission
		structure includes a corresponding resistor.
Claim 4	Claim 1	Patent '222 claims a method wherein the resistor is adjacent the at
		least one conductive layer.
Claim 5	Claim 1	Patent '222 claims a method wherein the at least one emission
		structure comprises a plurality of lines of emission structures.
Claim 6	Claim 1	Patent '222 claims a method wherein the emission structure located
		along a first line of the plurality of lines is isolated from at least one
		emission structure located an adjacent, second line of the plurality of
		lines.
Claim 7	Claim 1	Patent '222 claims a method wherein the conductive material over
		the substrate is patterned.
Claim 8	Claim 1	Patent '222 claims a method wherein the at least one emission
		structure is formed from at least one of semiconductive or conductive
		materials.
Claim 9	Claim 10	Patent '222 claims a method wherein the at least one emission
		structure extends over a lateral (peripheral) edge of the at least one
		conductive structure.
Claim 10	Claim 1	Patent '222 claims a method for fabricating at least one emission
		structure, comprising forming at least one conductive structure that
		extends at least partially across a substrate, forming at least one
		emitter tip and a corresponding resistor adjacent to the at least one
		conductive structure, and substantially removing (patterning) at least
		a longitudinal portion of the at least one conductive structure along
		substantially an entire length thereof to define at least one
		conductive layer substantially perpendicular (parallel rows) to the
		substrate.
Claim 11	Claim 1	Patent '222 claims a method wherein the conductive material over
		the substrate is patterned.

Art Unit: 2879

Claim 12	Claim 1	Patent '222 claims a method wherein the at least one emission
		structure is formed from at least one of semiconductive or conductive
		materials.
Claim 13	Claim 1	Patent '222 claims a method wherein the at least one
		emission/resistor structure is formed from at least one of
		semiconductive or conductive materials.
Claim 14	Claim 14	Patent '222 claims a method wherein forming the at least one emitter
		tip comprises disposing at least one layer comprising at least one of
		semiconductive material and conductive material over the substrate
		and the at least one conductive structure, removing a longitudinal
		portion of at least one region of the at least one layer located over
		the at least one conductive structure to expose at least a
		substantially longitudinal portion of the at least one conductive
		structure, and patterning at least one remaining portion of the at least
		one layer.
Claim 15	Claim 14	Patent '222 claims a method wherein at least one emitter tip is
		defined.
Claim 16	Claim 14	Patent '222 claims a method including a corresponding resistor.
Claim 17	Claim 10	Patent '222 claims a method wherein the substantially removing
		comprises leaving at least a lateral edge (conductive traces) of the at
		least one conductive structure along substantially the entire length
		thereof
Claim 18	Claim 10	Patent '222 claims a method wherein the at least one emission
		structure extends over a lateral (peripheral) edge of the at least one
		conductive structure.
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## **Contact Information**

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Mariceli Santiago whose telephone number is (571) 272-2464. The examiner can normally be reached on Monday-Friday from 9:30 AM to 6:00 PM.

**Art Unit: 2879** 

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nimesh Patel, can be reached on (571) 272-2457. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Page 5

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about PAIR system, see <a href="http://pair-direct.uspto.gov">http://pair-direct.uspto.gov</a>. Should you have questions on access to Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Mariceli Santiago Patent Examiner Art Unit 2879